

Switching Diode

Lead free product
Halogen-free type

BAS16HT1GH



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	VR	75	Vdc
Peak Forward Current	IF	200	mAdc
Peak Forward Surge Current	IFM(surge)	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max.	Unit
Total Device Dissipation FR-5 Board, TA=25°C Derate above 25°C	PD	200 1.57	mW mW / °C
Thermal Resistance, Junction to Ambient	RθJA	635	°C / W
Junction and Storage Temperature	TJ,TSTG	150	°C

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

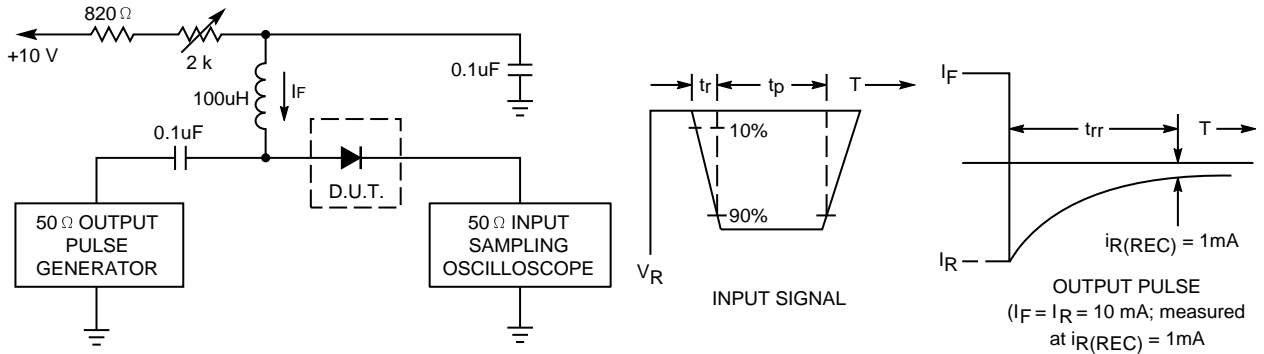
Characteristic	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Reverse Breakdown Voltage (IBR=100uAdc)	V(BR)	75	-	Vdc
Forward Voltage (IF=1.0 mAdc) (IF=10 mAdc) (IF=50 mAdc) (IF=150 mAdc)	VF	-	715 855 1000 1250	mVdc
Reverse Voltage Leakage Current (VR=75 Vdc) (VR=75 Vdc, TJ=150°C) (VR=25 Vdc, TJ=150°C)	IR	-	1.0 50 30	uAdc
Junction Capacitance (VR=0, f=1.0MHZ)	CJ	-	2.0	pF
Reverse Recovery Time (IF=10 mAdc, to VR = 5.0 Vdc, RL=500Ω)	trr	-	6.0	nS
Forward Recovery Voltage (IF=10 mAdc, tr=20nS)	VFR	-	1.75	Vdc
Stored Charge (IF=10 mAdc, to VR = 5.0 Vdc, RL=500Ω)	QS	-	45	pC

NOTE : FR-5=1.0 x 0.75 x 0.062in.

FIGURE 1. RECOVERY TIME EQUIVALENT TEST CIRCUIT



- Notes: 1. A 2.0kΩ variable resistor adjusted for a Forward Current (I_F) of 10mA.
 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10mA.
 3. $t_p \gg t_{rr}$

FIGURE 2. FORWARD VOLTAGE

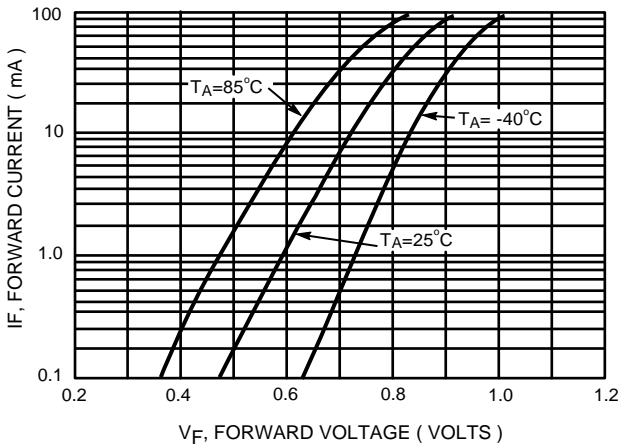


FIGURE 3. LEAKAGE CURRENT

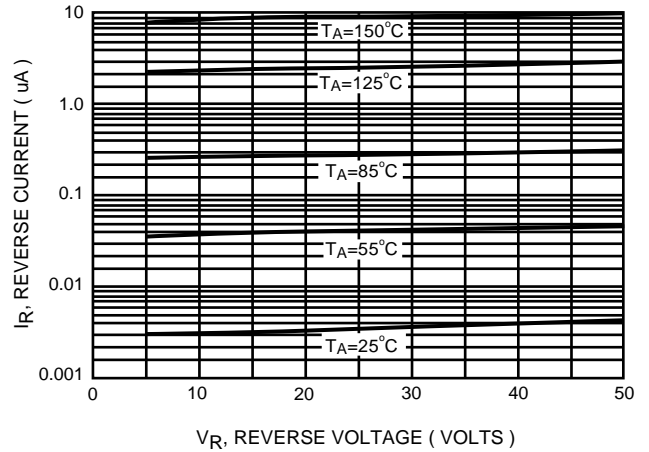


FIGURE 4. CAPACITANCE

